

20th RD50 Workshop (Bari)

Wednesday 30 May 2012

Material and Defect Characterization (09:15 - 11:40)

-Conveners: Mara Bruzzi; Mara Bruzzi

time	[id] title	presenter
09:15	[24] Deep levels roles in non-equilibrium conductivity in irradiated Si.	Prof. VAITKUS, Juozas
09:35	[20] Life time determination of free charge carriers in irradiated silicon sensors	POEHLSEN, Thomas
09:55	Coffee Break	
10:25	[1] Temperature dependence of reverse current of irradiated Si detectors	Dr VERBITSKAYA, Elena
10:45	[39] Evaluation of electron and hole detrapping in irradiated silicon sensors	GABRYSCH, Markus
11:05	[48] Shallow levels analysis in n-type MCZ Si detectors after mixed irradiation	Prof. BRUZZI, Mara BRUZZI, Mara
11:20	[29] Discussion on Material and Defect Characterization	Prof. BRUZZI, Mara BRUZZI, Mara